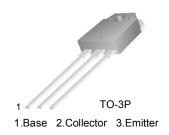


October 2008

FJA3835 NPN Epitaxial Silicon Transistor

- Power Amplifier
- High Current Capability : I_C=8A
- High Power Dissipation
- Wide S.O.A



Absolute Maximum Ratings* Ta = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{CBO}	Collector-Base Voltage	200	V	
V _{CEO}	Collector-Emitter Voltage	120	V	
V _{EBO}	Emitter-Base Voltage	8	V	
I _C	Collector Current (DC)	8	Α	
I _{CP}	Collector Current (Pulse)	16	Α	
P _C	Collector Dissipation (T _C =25°C)	80	W	
TJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 55 ~ 150	°C	

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics* T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =5mA, I _E =0	200			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =10mA, R _{BE} =∞	120			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =5mA, I _C =0	8			V
I _{CBO}	Collector Cut-off Current	V _{CB} =80V, I _E =0			0.1	mA
I _{EBO}	Emitter Cut-off Current	V _{EB} =4V, I _C =0			0.1	mA
h _{FE}	* DC Current Gain	V _{CE} =4V, I _C =3A	120		250	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =3A, I _B =0.3A			0.5	V
V _{BE} (sat)	Base-Emitter On Voltage	I _C =3A, I _B =0.3A			1.2	V
f _T	Current Gain Bandwidth Product	V _{CE} =5V, I _C =1A		30		MHz
C _{ob}	Output Capacitance	V _{CB} =10V, f=1MHz		210		pF
t _{ON}	Turn On Time	V _{CC} =20V,		0.26		μS
t _F	Fall Time	I _C =1A=10I _{B1} =-10I _{B2}		0.68		μS
t _{STG}	Storage Time	R _L =20Ω		6.68		μS

^{*} Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Characteristics

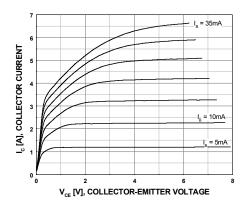


Figure 1. Static Characterstic

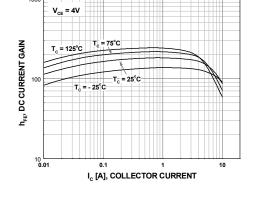


Figure 2. DC current Gain

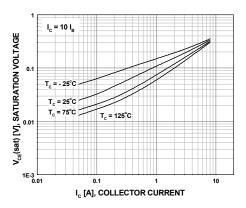


Figure 3. Collector-Emitter Saturation Voltage

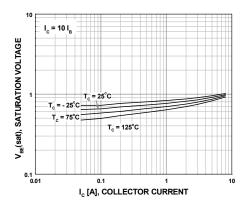


Figure 4. Base-Emitter Saturation Voltage

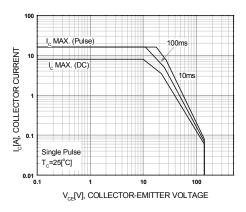


Figure 5. Safe Operating Area

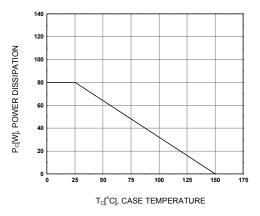
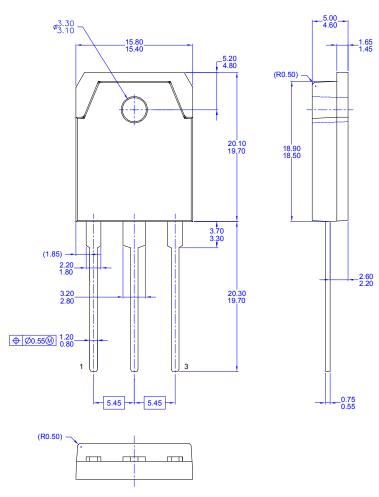


Figure 6. Power Derating

Package Dimension (TO-3P)



NOTES:

- NOTES:

 A) THIS PACKAGE CONFORMS TO EIAJ
 SC-65 PACKAGING STANDARD.

 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONING AND TOLERANCING PER
 ASME14.5 1973.

 D) DIMENSIONS ARE EXCLUSIVE OF BURRS,
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 E) DRAWING FILE NAME: TO3P03AREV2.





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